

IN THE CLAIMS:

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

1.-21. (Canceled)

22. (Currently Amended) An electron source comprising:
a substrate;
~~structure and at least one electron-emitting device arranged on said substrate, wherein said substrate structure is the substrate structure according to claim 1 or 9 a first insulating material film disposed on said substrate;~~
a second insulating material film laminated on said first insulating material film; and
a film containing an electron-emitting portion laminated on said second insulating material film,
wherein said first insulating material film comprises a plurality of metallic oxide particles having an average particle size within a range of 6nm to 60nm as expressed in a median value.

23. (Currently Amended) The electron source according to claim 22, wherein ~~each of said at least one electron-emitting device is an electron-emitting device~~

~~comprising a conductive said film containing an electron-emitting portion constitutes at least one electron-emitting device.~~

24. (Currently Amended) The electron source according to claim [[22]]
23, wherein ~~said the~~ at least one electron-emitting device is a plurality of electron-emitting devices that are matrix-wired by a plurality of row-directional wirings and a plurality of column directional wirings.

25. (Currently Amended) The electron source according to claim [[22]]
23, wherein ~~said the~~ at least one electron-emitting device is an electron-emitting device comprising a conductive film comprising an electron-emitting portion between one pair of electrodes.

26. (Currently Amended) The electron source according to claim 25, wherein the at least one electron-emitting device is a plurality of electron-emitting devices that are matrix-wired by a plurality of row-directional wirings and a plurality of column directional wirings,

wherein ~~said the~~ one pair of electrodes are composed of a material comprising platinum as a principal component, and
wherein ~~said the~~ wirings are composed of a material comprising silver as a principal component.

27. (Currently Amended) An image display apparatus comprising:

an envelope, at least one electron-emitting device disposed in said envelope on [[a]] said substrate structure; and

an image display member, for displaying images by irradiation of at least one electron from said at least one electron-emitting device, wherein the said substrate structure is the said substrate structure according to claim [[1 or 9]] 22.

28. (Currently Amended) The image display apparatus according to claim 27, wherein said the at least one electron-emitting device is an electron-emitting device comprising a conductive film comprising an electron-emitting portion.

29. (Currently Amended) The image display apparatus according to claim 27, wherein said the at least one electron-emitting device is a plurality of electron-emitting devices that are matrix-wired by a plurality of row-directional wirings and a plurality of column directional wirings.

30. (Currently Amended) The image display apparatus according to claim 27, wherein each of said the electron-emitting devices is an electron-emitting device comprising a conductive film comprising an electron-emitting portion between one pair of electrodes.

31. (Currently Amended) The image display apparatus according to claim 30, wherein the at least one electron-emitting device is a plurality of electron-

emitting devices that are matrix-wired by a plurality of row-directional wirings and a plurality of column directional wirings,

wherein said the one pair of electrodes are composed of a material comprising platinum as a principal component, and

wherein said the wirings are composed of a material comprising silver as a principal component.

32. (New) The electron source according to claim 22, wherein said first insulating material film further comprises phosphorus.

33. (New) The electron source according to claim 22, wherein said first insulating material film comprises phosphorus in 1 weight portion to 10 weight portions.

34. (New) The electron source according to claim 22, wherein a thickness of said first insulating material film is within a range of 200 nm to 600 nm.

35. (New) The electron source according to claim 22, wherein a thickness of said first insulating material film is within a range of 300 nm to 400 nm.

36. (New) The electron source according to claim 22, wherein a thickness of said second insulating material is within a range of 20 nm to 150 nm.

37. (New) The electron source according to claim 22, wherein a thickness of said second insulating material is within a range of 40 nm to 100 nm.

38. (New) The electron source according to claim 22, wherein said first insulating material film comprises SiO_2 .

39. (New) The electron source according to claim 22, wherein said second insulating material film comprises SiO_2 .

40. (New) The electron source according to claim 22, wherein the average particle size as expressed in the median value is within a range of 15 nm to 30 nm.

41. (New) The electron source according to claim 22, wherein the metallic oxide particles are electron conduction oxide particles.

42. (New) The electron source according to claim 22, wherein the metallic oxide particles are metallic oxide particles chosen from at least one of the oxides of Fe, Ni, Cu, Pd, Ir, In, Sn, Sb and Re.

43. (New) The electron source according to claim 22, wherein the metallic oxide particles are particles of SnO_2 .

44. (New) The electron source according to claim 22, wherein said substrate is a substrate comprising sodium.